

Single N-channel MOSFET

ELM14410AA-N

General description

ELM14410AA-N uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate resistance.

Features

- $V_{ds}=30V$
- $I_d=18A$ ($V_{gs}=10V$)
- $R_{ds(on)} < 5.5m\Omega$ ($V_{gs}=10V$)
- $R_{ds(on)} < 6.2m\Omega$ ($V_{gs}=4.5V$)

Maximum absolute ratings

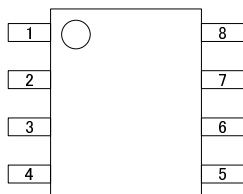
Parameter	Symbol	Limit	Unit	Note	
Drain-source voltage	V_{ds}	30	V		
Gate-source voltage	V_{gs}	± 12	V		
Continuous drain current	I_d	$T_a=25^\circ C$	18	A	1
		$T_a=70^\circ C$	15		
Pulsed drain current	I_{dm}	80	A	2	
Power dissipation	P_d	$T_a=25^\circ C$	3.0	W	
		$T_a=70^\circ C$	2.1		
Junction and storage temperature range	T_j, T_{stg}	-55 to 150	$^\circ C$		

Thermal characteristics

Parameter		Symbol	Typ.	Max.	Unit	Note
Maximum junction-to-ambient	$t \leq 10s$	$R\theta_{ja}$	31	40	$^\circ C/W$	1
Maximum junction-to-ambient	Steady-state		59	75	$^\circ C/W$	
Maximum junction-to-lead	Steady-state	$R\theta_{jl}$	16	24	$^\circ C/W$	3

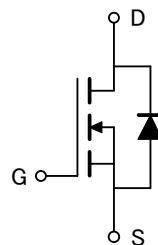
Pin configuration

SOP-8 (TOP VIEW)



Pin No.	Pin name
1	SOURCE
2	SOURCE
3	SOURCE
4	GATE
5	DRAIN
6	DRAIN
7	DRAIN
8	DRAIN

Circuit



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Electrical characteristics

T_a=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	BV _{dss}	I _d =250 μA, V _{gs} =0V	30			V
Zero gate voltage drain current	I _{dss}	V _{ds} =24V V _{gs} =0V		0.005	1.000	μA
		T _j =55°C			5.000	
Gate-body leakage current	I _{gss}	V _{ds} =0V, V _{gs} =±12V			100	nA
Gate threshold voltage	V _{gs(th)}	V _{ds} =V _{gs} , I _d =250 μA	0.8	1.1	1.5	V
On state drain current	I _{d(on)}	V _{gs} =4.5V, V _{ds} =5V	80			A
Static drain-source on-resistance	R _{ds(on)}	V _{gs} =10V		4.7	5.5	mΩ
		I _d =18A	T _j =125°C	6.4	7.4	
		V _{gs} =4.5V, I _d =15A		5.2	6.2	mΩ
Forward transconductance	G _{fs}	V _{ds} =5V, I _d =18A		102		S
Diode forward voltage	V _{sd}	I _s =1A, V _{gs} =0V		0.64	1.00	V
Max. body-diode continuous current	I _s				4.5	A
DYNAMIC PARAMETERS						
Input capacitance	C _{iss}			9130	10500	pF
Output capacitance	C _{oss}	V _{gs} =0V, V _{ds} =15V, f=1MHz		625		pF
Reverse transfer capacitance	C _{rss}			387		pF
Gate resistance	R _g	V _{gs} =0V, V _{ds} =0V, f=1MHz		0.4	0.5	Ω
SWITCHING PARAMETERS						
Total gate charge	Q _g			72.4	85.0	nC
Gate-source charge	Q _{gs}	V _{gs} =10V, V _{ds} =15V, I _d =18A		13.4		nC
Gate-drain charge	Q _{gd}			16.8		nC
Turn-on delay time	t _{d(on)}			11.0	15.0	ns
Turn-on rise time	t _r	V _{gs} =10V, V _{ds} =15V		7.0	11.0	ns
Turn-off delay time	t _{d(off)}	R _l =0.83 Ω, R _{gen} =3 Ω		99.0	135.0	ns
Turn-off fall time	t _f			13.0	19.5	ns
Body diode reverse recovery time	t _{rr}	I _f =18A, dI/dt=100A/μs		33.0	40.0	ns
Body diode reverse recovery charge	Q _{rr}	I _f =18A, dI/dt=100A/μs		22.2	30.0	nC

NOTE :

1. The value of R_{θja} is measured with the device mounted on 1in² FR-4 board of 2oz. Copper, in still air environment with T_a=25°C. The value in any given applications depends on the user's specific board design, The current rating is based on the t ≤ 10s thermal resistance rating.
2. Repetitive rating, pulse width limited by junction temperature.
3. The R_{θja} is the sum of the thermal impedance from junction to lead R_{θjl} and lead to ambient.
4. The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5%max.
5. These tests are performed with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_a=25°C. The SOA curve provides a single pulse rating.

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Typical electrical and thermal characteristics

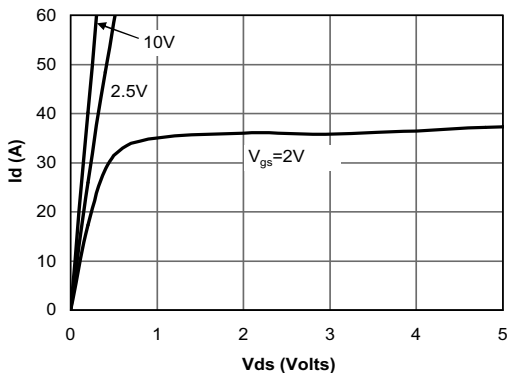


Figure 1: On-Region Characteristics

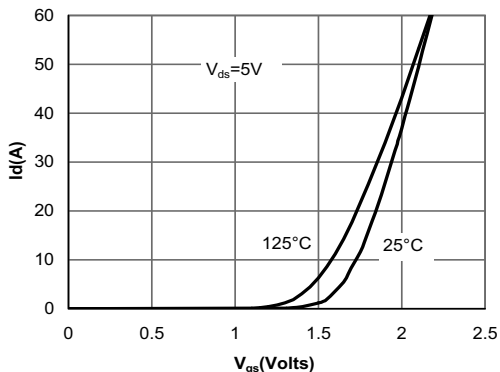


Figure 2: Transfer Characteristics

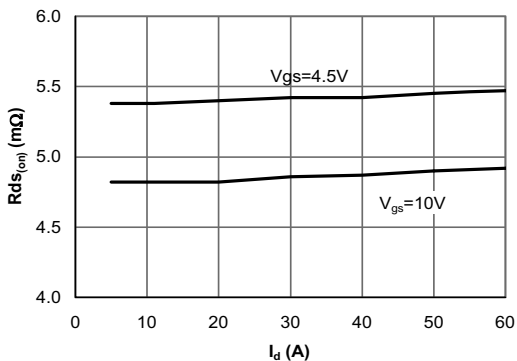


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

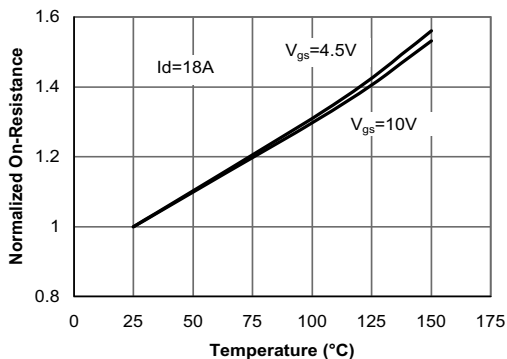


Figure 4: On-Resistance vs. Junction Temperature

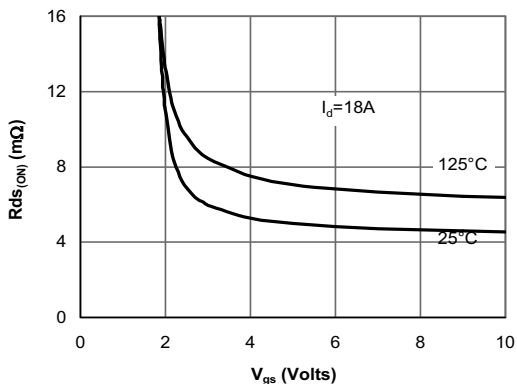


Figure 5: On-Resistance vs. Gate-Source Voltage

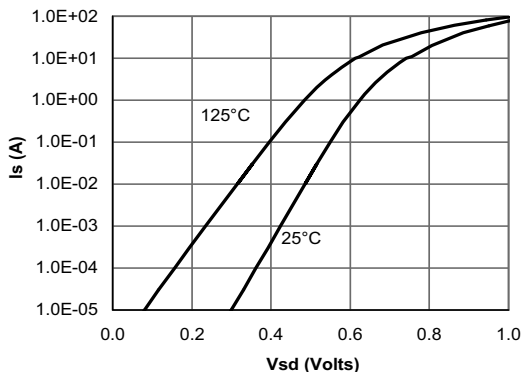


Figure 6: Body-Diode Characteristics

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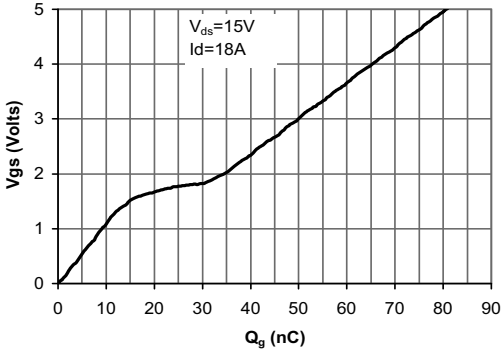


Figure 7: Gate-Charge Characteristics

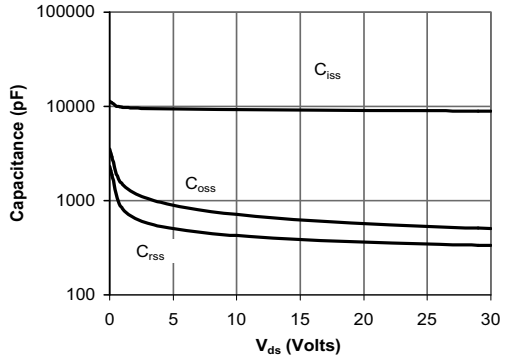


Figure 8: Capacitance Characteristics

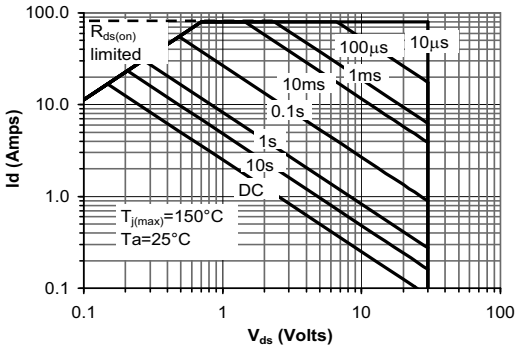


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

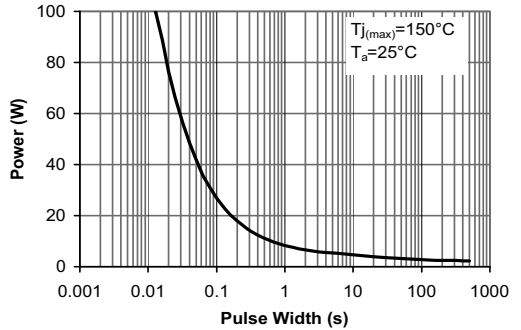


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

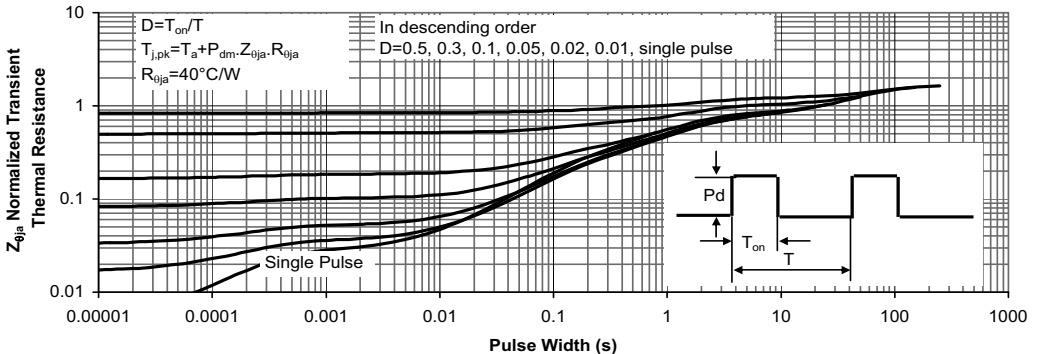


Figure 11: Normalized Maximum Transient Thermal Impedance